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(54) **GALLIUM NITRIDE (GAN) LAYER ON SUBSTRATE CARBURIZATION FOR INTEGRATED CIRCUIT TECHNOLOGY**

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(57) **ABSTRACT**  
Gallium nitride (GaN) layer on substrate carburization for integrated circuit technology is described. In an example, an integrated circuit structure includes a substrate including silicon. A layer comprising silicon and carbon is above the substrate. A layer comprising gallium and nitrogen is on the layer comprising silicon and carbon.

